

MAIN CHARACTERISTICS

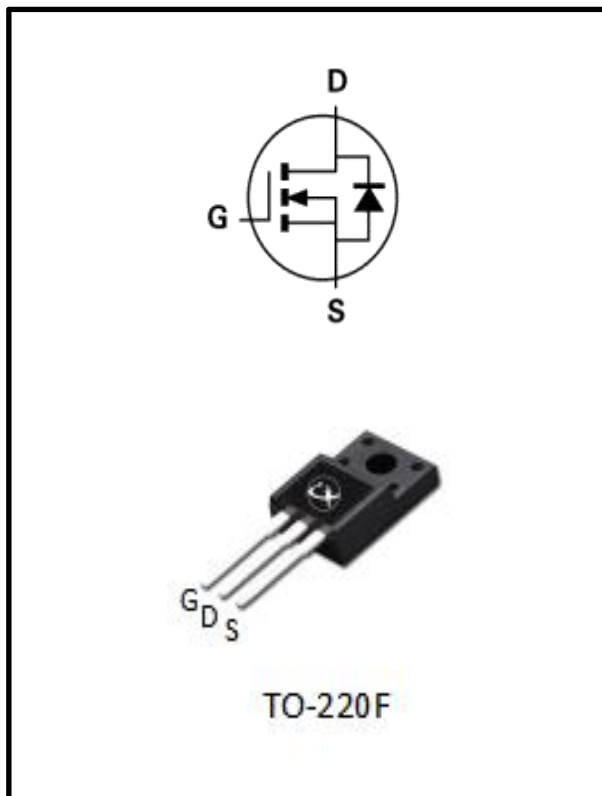
I_D	150A
V_{DSS}	85V
$R_{DS(on)-Typ@ V_{GS}=10V}$	3.9mΩ

FEATURES

- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- Halogen-free and RoHS-compliant

APPLICATIONS

- Motor Driving in Power Tool, E-vehicle, Robotics
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Power Management in Telecom., Industrial Automation, CE



Product specification classification

Part Number	Package	Mode Name	Pack
LG150N085AF	TO-220F	LG150N085AF	Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	85	V
Gate-Source Voltage	V_{GS}	±20	V
Continue Drain Current	I_D	150	A
Pulsed Drain Current (Note1)	I_{DM}	515	A
Power Dissipation	P_D	192	W
Single Pulse Avalanche Energy	E_{AS}	434	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.65	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	45	°C/W

Note1:Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	BV_{DSS}	85	-	-	V
Drain-Source Leakage Current	$V_{DS} = 80\text{V}, V_{GS} = 0 \text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$	$R_{DS(on)}$	-	3.9	5	m Ω
Forward Transconductance	$V_{DS}=5\text{V}, I_D=20\text{A}$	g_{FS}	-	43	-	S
Input Capacitance	$V_{DS}=40\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$	C_{iss}	-	4083	-	pF
Output Capacitance		C_{oss}	-	1313	-	pF
Reverse Transfer Capacitance		C_{rss}	-	42	-	pF
Turn-on Delay Time(Note2)	$V_{GS} = 10\text{V}, V_{DS} = 40\text{V}$ $R_L = 2.0\Omega, R_{GEN} = 3\Omega$	$t_{d(ON)}$	-	18.9	-	ns
Rise Time(Note2)		t_r	-	28	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	38	-	ns
Fall Time(Note2)		t_f	-	13.1	-	ns
Total Gate Charge(Note2)	$V_{DS}=40\text{V}, V_{GS}=10\text{V}, I_D=20\text{A}$	Q_G	-	62	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	21	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	13.8	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	150	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	515	A
Drain-Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_S=1\text{A}, T_J=25^\circ\text{C}$	V_{SD}	-	-	1	V
Reverse Recovery Time	$I_S = I_F, I_{SD}=20\text{A}, V_{GS} = 0 \text{ V},$	t_{rr}	-	57	-	ns
Reverse Recovery Charge	$di / dt = 100 \text{ A}/\mu\text{s} \text{ (Note3)}$	Q_{rr}	-	85	-	nC

Note2:Pulse test: 300 μ s pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

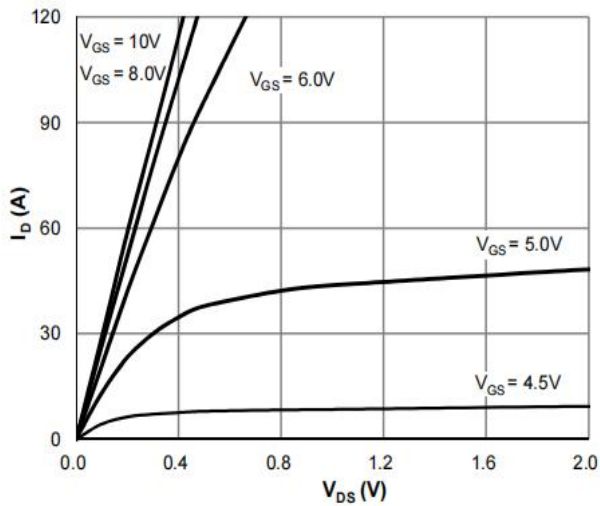


Figure 1: Saturation Characteristics

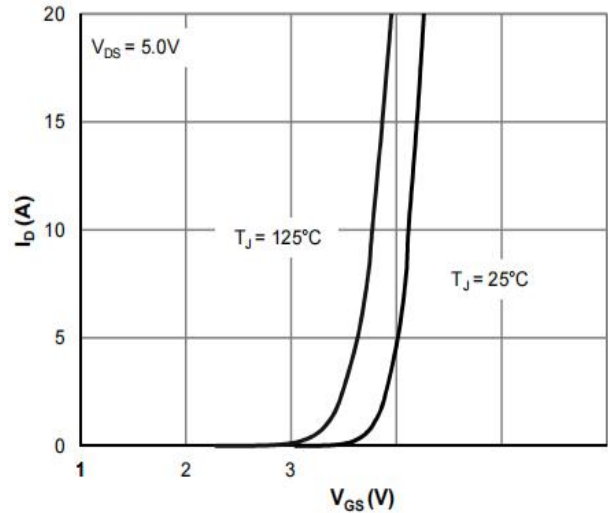


Figure 2: Transfer Characteristics

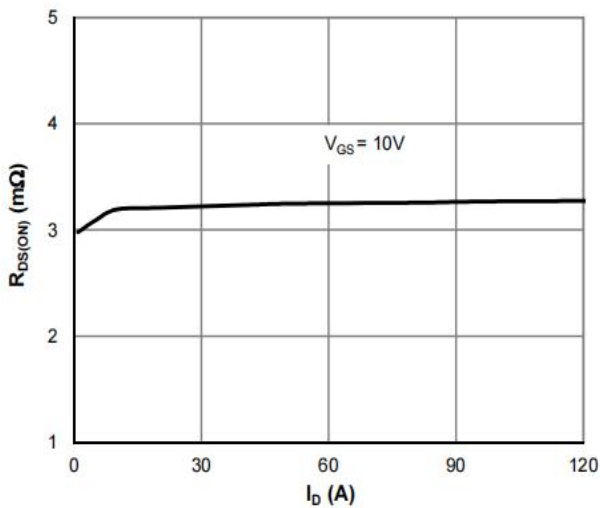


Figure 3: $R_{DS(ON)}$ vs. Drain Current

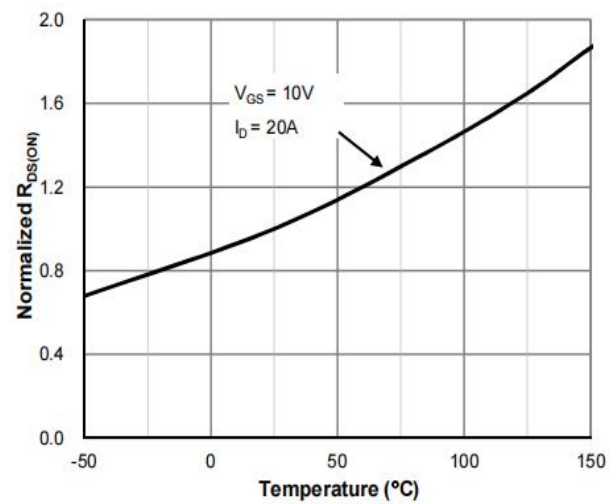


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

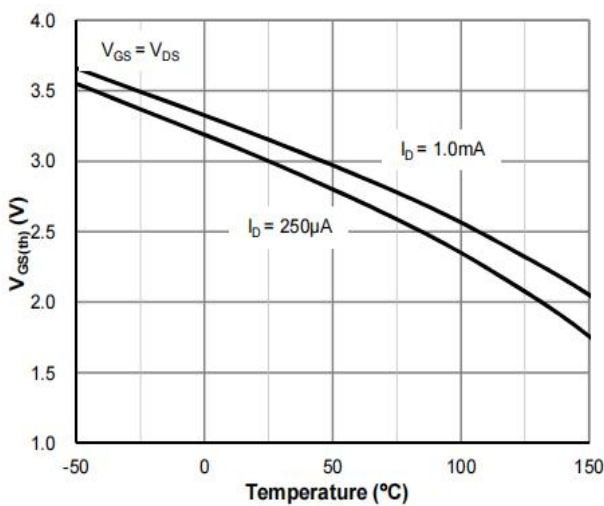


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

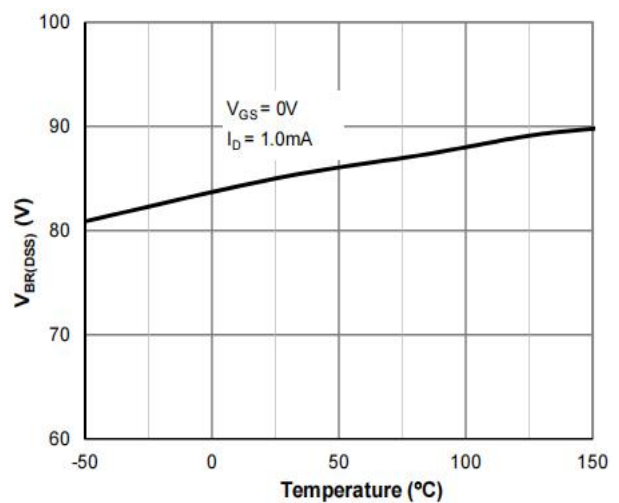


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

RATINGS AND CHARACTERISTIC CURVES

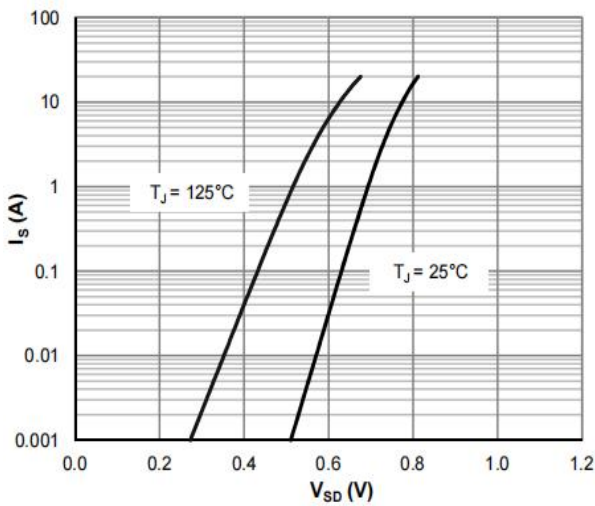


Figure 7: Body-Diode Characteristics

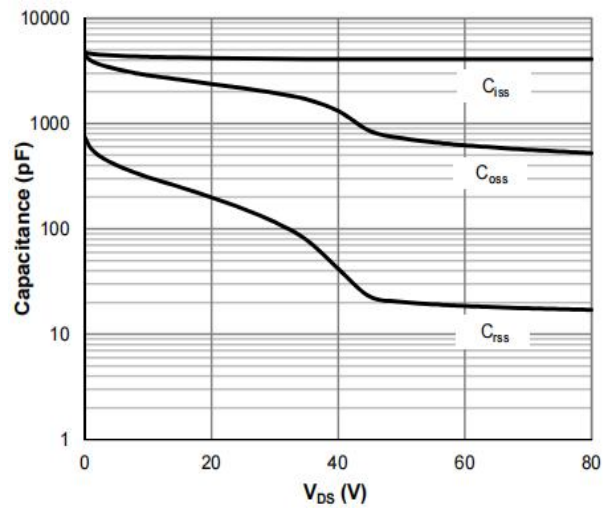


Figure 8: Capacitance Characteristics

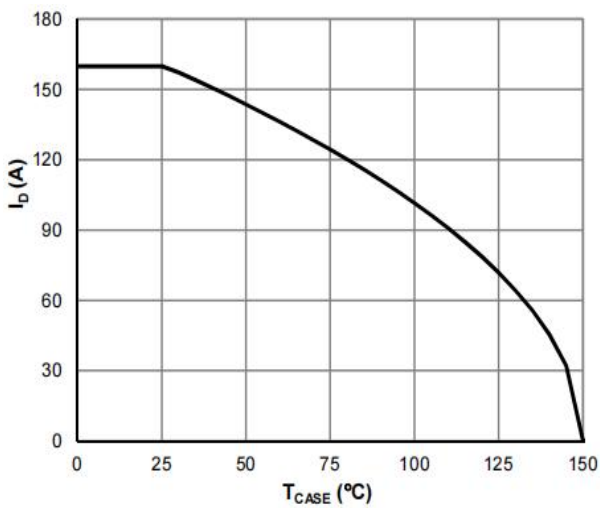


Figure 9: Current De-rating

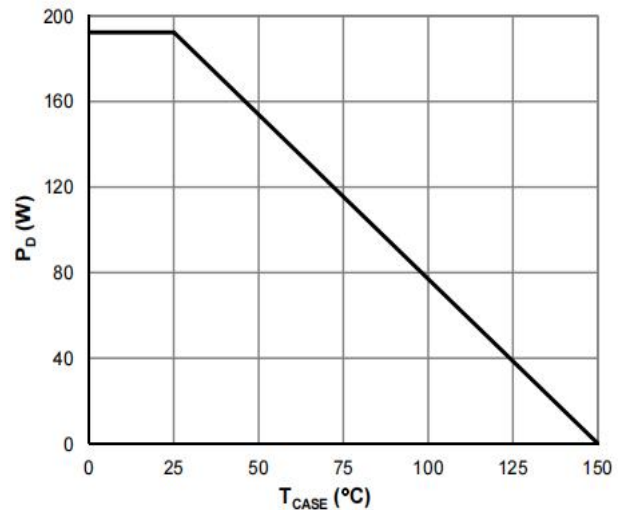


Figure 10: Power De-rating

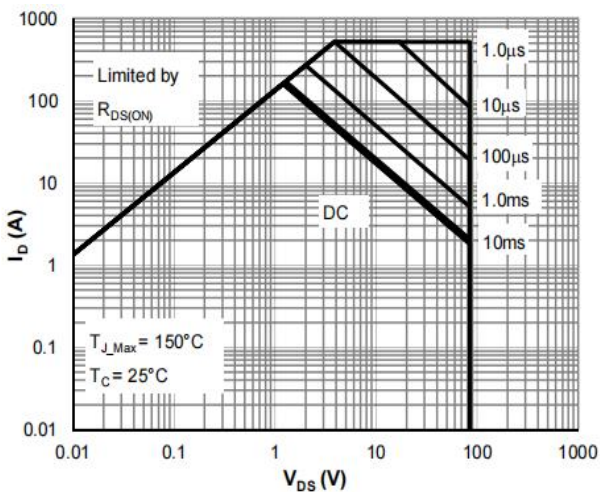


Figure 11: Maximum Safe Operating Area

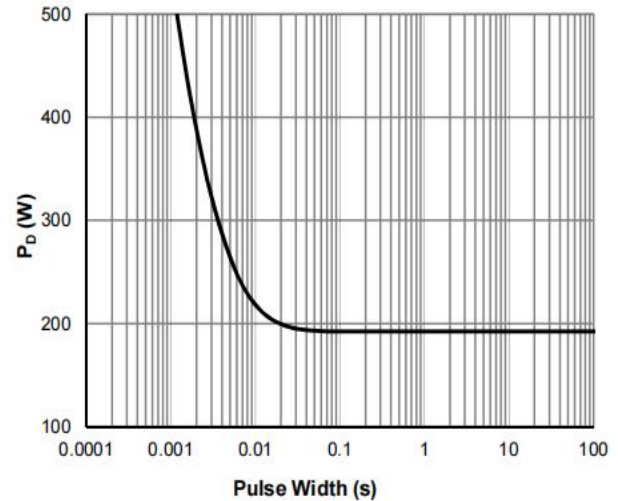
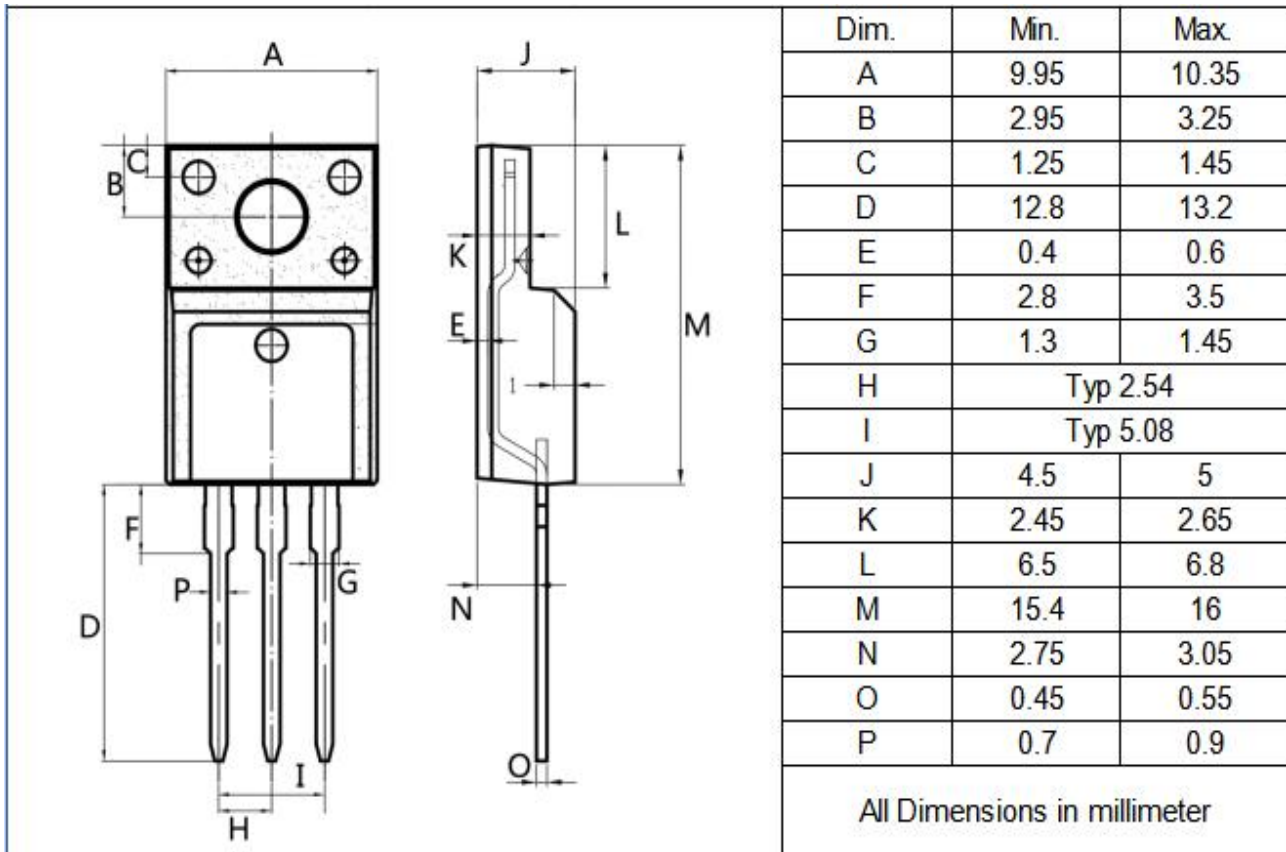
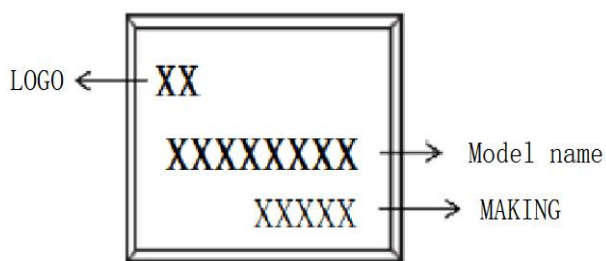


Figure 12: Single Pulse Power Rating, Junction-to-Case

TO-220F



Marking on the body



MAKING:

X X X XX

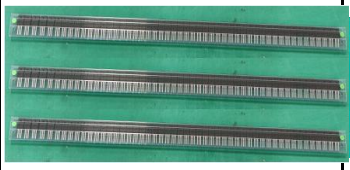
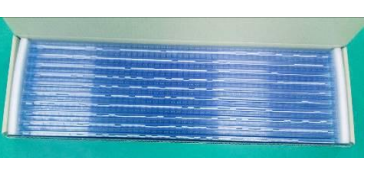
Assembly code (e.g : AB,CD,.....)

Material -Code
(H:No halogen A:ordinary)

month - code (WW: 1-1, 10-A...)

Year - code
(Y: Last digit of year & A:2012,B:2013. ...)

packing instruction

PKG	Minimal Package	Box	Carton
TO-220F			
	50pcs/pdpe	1000pcs/box	5000pcs/carton



LG150N085AF

N-Channel SGT Power MOSFET

Notice

All product, product specifications and data are subject to change without notice to improve. The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying power exceeding normal rated

power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

<http://www.lxmicro.com>

Revision History

Rev	Changes	Date
1.0	First version	2025-11-20